

FORM PTO-1449 (REV. 1-84)		U.S. DEPARTMENT OF COMMERCE PATENT & TRADEMARK OFFICE							CASE NO. 7-1		SERIAL NO. 10/164,202	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)									APPLICANT: J. M. Hergenrother et al.			
									FILING DATE: June 6, 2002		GROUP: 2812	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME		CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
AA	6	1	9	7	6	4	1	3/01	Hergenrother et al.		438	268	-----
AB													
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AI													
AJ													
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	COUNTRY/AUTHOR		CLASS	SUB-CLASS	TRANSL'N YES NO
AL													
AM													
AN													
AO													
AP													

OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>Dh</i>	AR	Ishiwara et al., Lateral solid phase epitaxy in selectively P-doped amorphous Si films, Appl. Phys. Lett., Vol. 49, No. 20, p. 1365 (Nov. 1986) (Abstract only)
	AS	Ishiwara et al., Selective Surface Doping Method of P Atoms in Lateral Solid Phase Epitaxy..., Jpn. J. Appl. Phys., Vol. 31, p. 1695 (June 1992)
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	AV	Choi et al., Ultra-thin-Body SOI MOSFET for Deep-sub-10nm Micron Era, IEEE Electron Dev. Lett., Vol. 21, No. 5, p. 254 (May 2000)
	AW	Subramanian et al., A Bulk-Si-compatible Ultrathin SOI Technology for sub-100nm MOSFETs, Device Research Conf. Tech. Dig., p. 28 (1999)
	AX	Hergenrother et al., The Vertical Replacement-Gate...Gate Length, IEDM Tech. Dig., p. 75 (1999)
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EXAMINER:
SHEET 1 OF 1

DATE CONSIDERED:

July - 2004